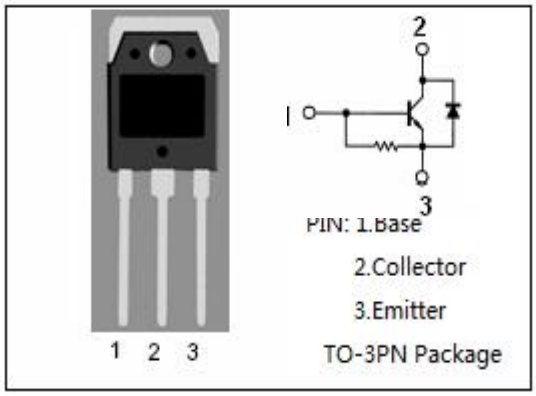
# isc Silicon NPN Power Transistor — 2SD1426




## DESCRIPTION

- High Breakdown Voltage
- High Switching Speed
- Built-in damper diode
- Low Saturation Voltage
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## APPLICATIONS

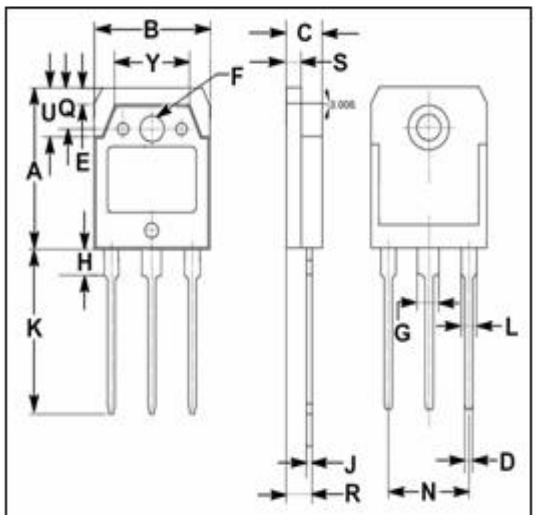
- Designed for use in horizontal deflection circuits of colour TV receivers.

## ABSOLUTE MAXIMUM RATINGS ($T_a$=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT |
|---|---|---|---|
| $V_{CBO}$ | Collector-Base Voltage | 1500 | V |
| $V_{CEO}$ | Collector-Emitter Voltage | 600 | V |
| $V_{EBO}$ | Emitter-Base Voltage | 5 | V |
| $I_C$ | Collector Current-Continuous | 3.5 | A |
| $I_B$ | Base Current-Continuous | 1.0 | A |
| $P_C$ | Collector Power Dissipation @$T_C$=25℃ | 80 | W |
| $T_j$ | Junction Temperature | 150 | ℃ |
| $T_{stg}$ | Storage Temperature Range | -55-150 | ℃ |

## THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---|---|---|---|
| $R_{th\ j\text{-}c}$ | Thermal Resistance,Junction to Case | 1.56 | ℃/W |




| DIM | mm MIN | MAX |
|---|---|---|
| A | 19.60 | 20.30 |
| B | 15.50 | 15.70 |
| C | 4.70 | 4.90 |
| D | 0.90 | 1.10 |
| E | 1.90 | 2.10 |
| F | 3.40 | 3.60 |
| G | 2.90 | 3.20 |
| H | 3.20 | 3.40 |
| J | 0.595 | 0.605 |
| K | 19.80 | 20.70 |
| L | 1.90 | 2.20 |
| N | 10.89 | 10.91 |
| Q | 4.90 | 5.10 |
| R | 3.35 | 3.45 |
| S | 1.995 | 2.100 |
| U | 5.90 | 6.20 |
| Y | 9.90 | 10.10 |

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## ELECTRICAL CHARACTERISTICS

**$T_C$=25℃ unless otherwise specified**

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|
| $V_{(BR)EBO}$ | Emitter-Base Breakdown Voltage | $I_E$= 200mA; $I_C$= 0 | 5 | | | V |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C$= 3A; $I_B$= 0.8A | | | 8.0 | V |
| $V_{BE(sat)}$ | Base-Emitter Saturation Voltage | $I_C$= 3A; $I_B$= 0.8A | | | 1.5 | V |
| $h_{FE}$ | DC Current Gain | $I_C$= 0.5A ; $V_{CE}$= 5V | 8 | | | |
| $I_{CBO}$ | Collector Cutoff Current | $V_{CB}$= 500V; $I_E$= 0 | | | 10 | μA |
| $f_T$ | Transition Frequency | $I_C$= 0.1A ; $V_{CE}$= 10V; f= 1MHz | | 3 | | MHz |
| $C_{OB}$ | Output Capacitance | $I_E$= 0; $V_{CB}$= 10V; $f_{test}$= 1MHz | | 95 | | pF |
| $V_{ECF}$ | C-E Diode Forward Voltage | $I_F$= 3.5A | | | 2.0 | V |
| $t_f$ | Fall Time | $I_C$= 3A; $I_{B1}$= 0.8A | | | 1.0 | μs |